

## WHAT IS CLAIMED IS:

1. A camera comprising: /  
a main body;  
an eyepiece;  
a switching unit;  
an image receiver; and  
a display having a semiconductor device,  
wherein the semiconductor device comprises:  
a gate electrode formed over a substrate;  
a first insulating layer formed over the gate electrode;  
a second insulating layer formed over the first insulating layer;  
a semiconductor layer formed over the second insulating layer, the  
semiconductor layer having at least a channel region and at least one impurity  
region;  
an inorganic insulating layer formed over the semiconductor layer, the  
inorganic insulating layer being in contact with a portion of the impurity region;  
and  
an organic insulating layer formed over the inorganic insulating layer,  
the organic insulating layer being in contact with another portion of the  
impurity region.

2. A camera according to claim 1, wherein the gate electrode  
comprises at least one layer comprising a material selected from the group  
consisting of tantalum, molybdenum, titanium, chromium and silicon.

3. A camera comprising: /  
a main body;  
an eyepiece;  
a switching unit;  
an image receiver; and  
a display having a semiconductor device,  
wherein the semiconductor device comprises:  
a gate electrode formed over a substrate;

a first insulating layer comprising silicon nitride formed over the gate electrode;

a second insulating layer comprising silicon oxide formed over the first insulating layer;

a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;

an inorganic insulating layer formed over the semiconductor layer, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

4. A camera according to claim 3, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

5. A camera comprising:

a main body;

an eyepiece;

a switching unit;

an image receiver; and

a display having a semiconductor device,

wherein the semiconductor device comprises:

a gate electrode formed over a substrate;

a first insulating layer formed over the gate electrode, the first insulating layer having a thickness of 10-200nm;

a second insulating layer formed over the first insulating layer, the second insulating layer having a thickness of 50-300nm;

a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;

an inorganic insulating layer formed over the semiconductor layer, the

inorganic insulating layer being in contact with a portion of the impurity region;  
and

an organic insulating layer formed over the inorganic insulating layer,  
the organic insulating layer being in contact with another portion of the  
impurity region.

6. A camera according to claim 5, wherein the gate electrode  
comprises at least one layer comprising a material selected from the group  
consisting of tantalum, molybdenum, titanium, chromium and silicon.

7. A camera comprising:

a main body;

an eyepiece;

a switching unit;

an image receiver; and

a display having a semiconductor device,

wherein the semiconductor device comprises:

a gate electrode formed over a substrate;

a first insulating layer formed over the gate electrode;

a second insulating layer formed over the first insulating layer;

a semiconductor layer formed over the second insulating layer, the  
semiconductor layer having at least a channel region and at least one impurity  
region;

an inorganic insulating layer comprising silicon oxide formed over the  
semiconductor layer, the inorganic insulating layer being in contact with a  
portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer,  
the organic insulating layer being in contact with another portion of the  
impurity region.

8. A camera according to claim 7, wherein the gate electrode  
comprises at least one layer comprising a material selected from the group  
consisting of tantalum, molybdenum, titanium, chromium and silicon.

9. A camera comprising:  
a main body;  
an eyepiece;  
a switching unit;  
an image receiver; and  
a display having a semiconductor device,  
wherein the semiconductor device comprises:  
at least two gate electrodes formed over a substrate;  
a first insulating layer formed over the gate electrodes;  
a second insulating layer formed over the first insulating layer;  
a semiconductor layer formed over the second insulating layer, the  
semiconductor layer having at least a channel region and at least one impurity  
region;  
an inorganic insulating layer formed over the semiconductor layer, the  
inorganic insulating layer being in contact with a portion of the impurity region;  
and  
an organic insulating layer formed over the inorganic insulating layer,  
the organic insulating layer being in contact with another portion of the  
impurity region.

10. A camera according to claim 9, wherein each of the gate  
electrodes comprises at least one layer comprising a material selected from  
the group consisting of tantalum, molybdenum, titanium, chromium and  
silicon.

11. A camera comprising:  
a main body;  
an eyepiece;  
a switching unit;  
an image receiver; and  
a display having a driving circuit and a pixel circuit,  
wherein a plurality of thin film transistors formed in the pixel circuit,  
each of the thin film transistors comprising:  
a gate electrode formed over a substrate;

a first insulating layer formed over the gate electrode;  
a second insulating layer formed over the first insulating layer;  
a semiconductor layer formed over the second insulating layer, the semiconductor layer having at least a channel region and at least one impurity region;  
an inorganic insulating layer formed over the semiconductor layer, the inorganic insulating layer being in contact with a portion of the impurity region;  
and  
an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

12. A camera according to claim 11, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

13. A semiconductor device comprising:  
a gate electrode formed over a substrate;  
a first insulating layer formed over the gate electrode;  
a second insulating layer formed over the first insulating layer;  
at least a channel region and an impurity region formed over the second insulating layer;  
an inorganic insulating layer formed over the channel region and the impurity region, the inorganic insulating layer being in contact with a portion of the impurity region; and  
an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

14. A semiconductor device according to claim 13, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

15. A semiconductor device according to claim 13, wherein the semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player for a recording medium, a digital still camera, a front-type projector and a rear-type projector.

16. A semiconductor device comprising:  
a gate electrode formed over a substrate;  
a first insulating layer comprising silicon nitride formed over the gate electrode;  
a second insulating layer comprising silicon oxide formed over the first insulating layer;  
at least a channel region and an impurity region formed over the second insulating layer;  
an inorganic insulating layer formed over the channel region and the impurity region, the inorganic insulating layer being in contact with a portion of the impurity region; and  
an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

17. A semiconductor device according to claim 16, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

18. A semiconductor device according to claim 16, wherein the semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player for a recording medium, a digital still camera, a front-type projector and a rear-type projector.

19. A semiconductor device comprising:  
a gate electrode formed over a substrate;  
a first insulating layer formed over the gate electrode, the first

insulating layer having a thickness of 10-200nm;

a second insulating layer formed over the first insulating layer, the second insulating layer having a thickness of 50-300nm;

a channel region and an impurity regions formed over the second insulating layer;

an inorganic insulating layer formed over the channel region and the impurity region, the inorganic insulating layer being in contact with a portion of the impurity region; and

an organic insulating layer formed over the inorganic insulating layer, the organic insulating layer being in contact with another portion of the impurity region.

20. A semiconductor device according to claim 19, wherein the gate electrode comprises at least one layer comprising a material selected from the group consisting of tantalum, molybdenum, titanium, chromium and silicon.

21. A semiconductor device according to claim 19, wherein the semiconductor device is selected from the group consisting of a personal computer, a video camera, a mobile computer, a goggle-type display, a player for a recording medium, a digital still camera, a front-type projector and a rear-type projector.